

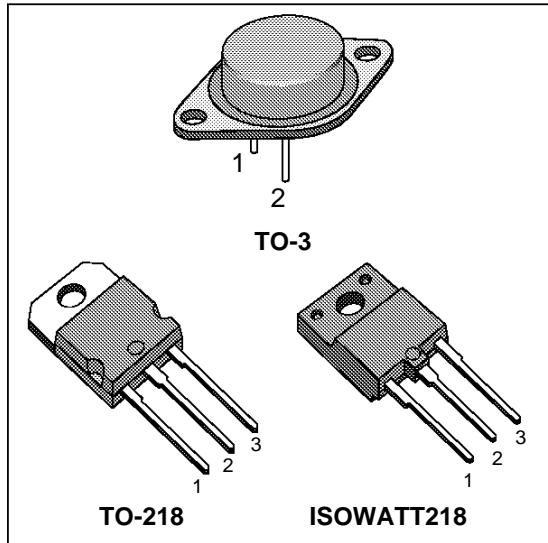
HIGH VOLTAGE IGNITION COIL DRIVER  
 NPN POWER DARLINGTON

PRELIMINARY DATA

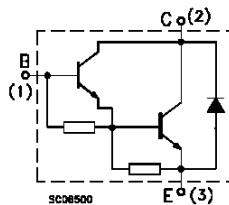
- VERY RUGGED BIPOLAR TECHNOLOGY
- HIGH OPERATING JUNCTION TEMPERATURE
- WIDE RANGE OF PACKAGES

**APPLICATIONS**

- HIGH RUGGEDNESS ELECTRONIC IGNITIONS



## INTERNAL SCHEMATIC DIAGRAM



for TO-3  
 Emitter: pin 2  
 Base: pin 1  
 Collector: tab

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value			Unit
		BU931	BU931P	BU931PFI	
V <sub>CES</sub>	Collector-Emitter Voltage ( $V_{BE} = 0$ )	500			V
V <sub>CEO</sub>	Collector-Emitter Voltage ( $I_B = 0$ )	400			V
V <sub>EBO</sub>	Emitter-Base Voltage ( $I_C = 0$ )	5			V
I <sub>C</sub>	Collector Current	15			A
I <sub>CM</sub>	Collector Peak Current	30			A
I <sub>B</sub>	Base Current	1			A
I <sub>BM</sub>	Base Peak Current	5			A
P <sub>tot</sub>	Total Dissipation at $T_c = 25^\circ\text{C}$	175	135	60	W
T <sub>stg</sub>	Storage Temperature	-65 to 200	-65 to 175	-65 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	200	175	175	°C

## THERMAL DATA

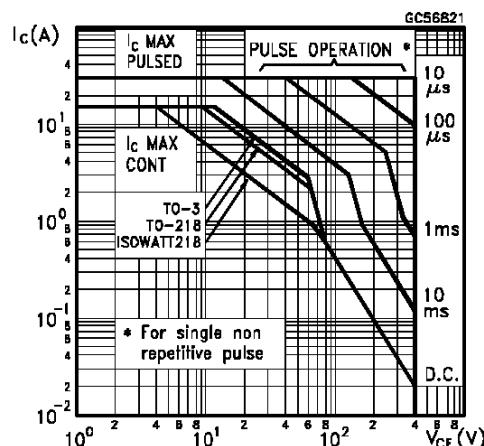
			TO-3	TO-218	ISOWATT218	
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1	1.1	2.5	°C/W

ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^\circ\text{C}$  unless otherwise specified)

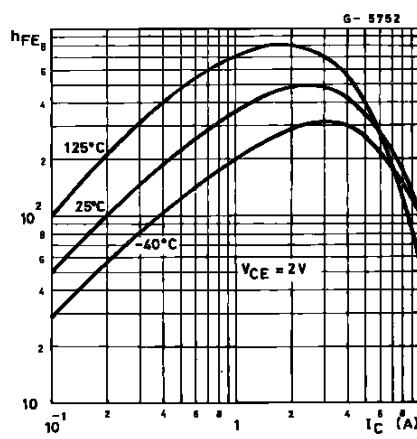
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current ( $V_{BE} = 0$ )	$V_{CE} = 500 \text{ V}$ $V_{CE} = 500 \text{ V} \quad T_j = 125^\circ\text{C}$			100 0.5	μA mA
I <sub>CEO</sub>	Collector Cut-off Current ( $I_B = 0$ )	$V_{CE} = 450 \text{ V}$ $V_{CE} = 450 \text{ V} \quad T_j = 125^\circ\text{C}$			100 0.5	μA mA
I <sub>EBO</sub>	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = 5 \text{ V}$			20	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage	$I_C = 100 \text{ mA} \quad L = 10 \text{ mH} \quad I_B = 0$ $V_{CLAMP} = \text{RATED } V_{CEO} \text{ (See FIG.4)}$	400			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	$I_C = 7 \text{ A} \quad I_B = 70 \text{ mA}$ $I_C = 8 \text{ A} \quad I_B = 100 \text{ mA}$ $I_C = 10 \text{ A} \quad I_B = 250 \text{ mA}$			1.6 1.8 1.8	V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	$I_C = 7 \text{ A} \quad I_B = 70 \text{ mA}$ $I_C = 8 \text{ A} \quad I_B = 100 \text{ mA}$ $I_C = 10 \text{ A} \quad I_B = 250 \text{ mA}$			2.2 2.4 2.5	V
h <sub>FE*</sub>	DC Current Gain	$I_C = 5 \text{ A} \quad V_{CE} = 10 \text{ V}$	300			
V <sub>F</sub>	Diode Forward Voltage	$I_F = 10 \text{ A}$			2.5	V
	Functional Test (see fig. 1)	$V_{CC} = 24 \text{ V} \quad V_{clamp} = 400 \text{ V} \quad L = 7 \text{ mH}$	8			A
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time (see fig. 3)	$V_{CC} = 12 \text{ V} \quad V_{clamp} = 300 \text{ V} \quad L = 7 \text{ mH}$ $I_C = 7 \text{ A} \quad I_B = 70 \text{ mA}$ $V_{BE} = 0 \quad R_{BE} = 47 \Omega$		15 0.5		μs μs

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

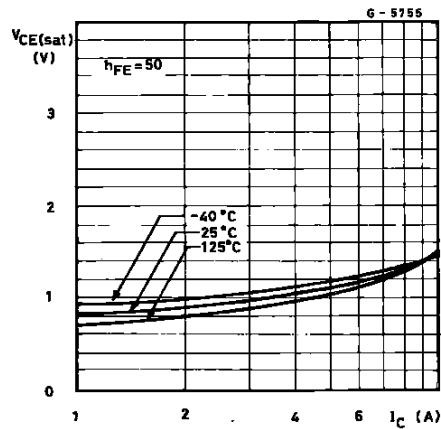
## Safe Operating Areas



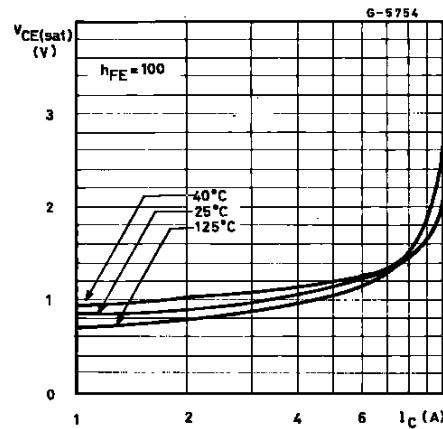
## DC Current Gain



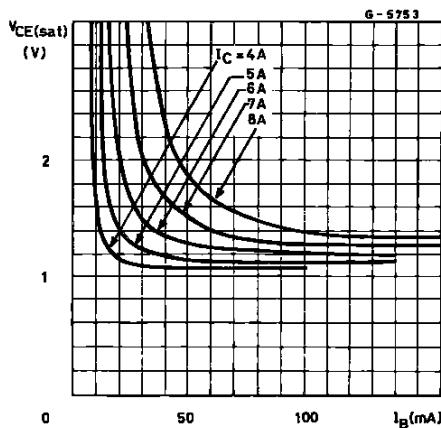
Collector-emitter Sturation Voltage



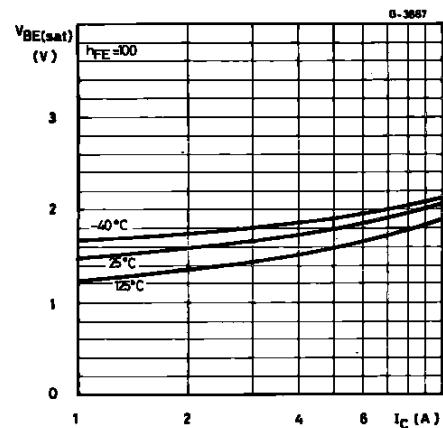
Collector-emitter Sturation Voltage



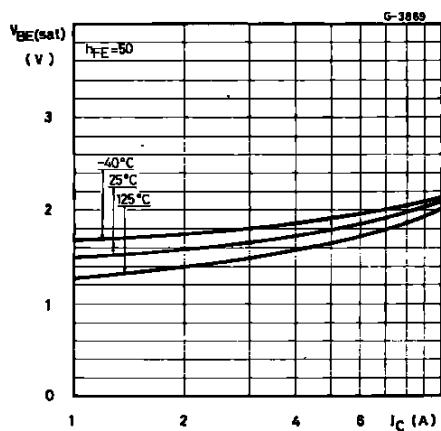
Collector-emitter Sturation Voltage



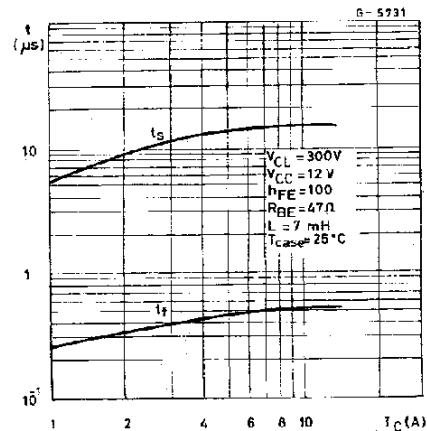
Base-emitter Sturation Voltage



Base-emitter Sturation Voltage



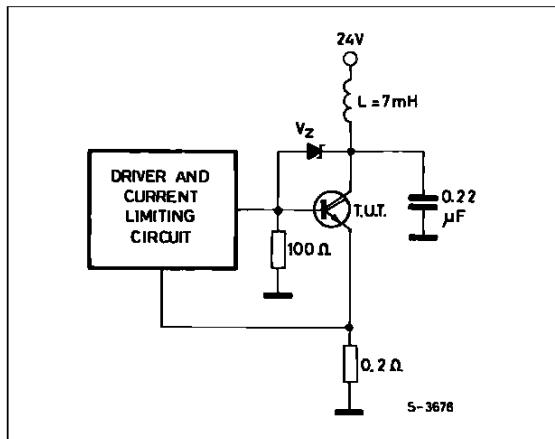
Switching Times Inductive Load



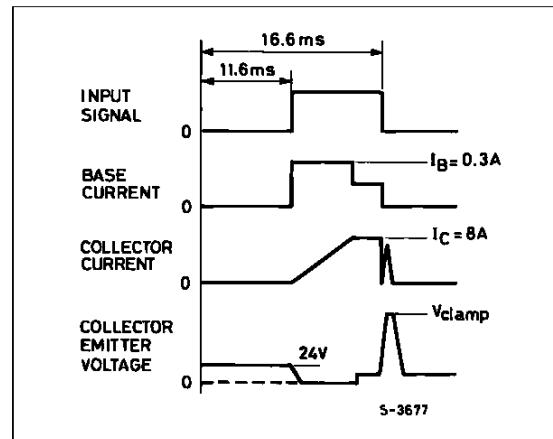
## BU931/BU931P/BU931PFI

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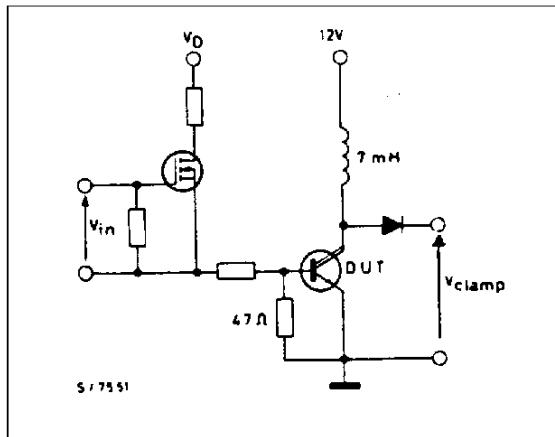
**FIGURE 1:** Functional Test Circuit



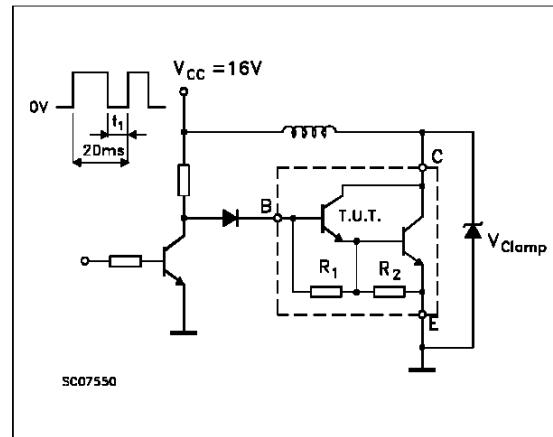
**FIGURE 2:** Functional Test Waveforms



**FIGURE 3:** Switching Time Test Circuit

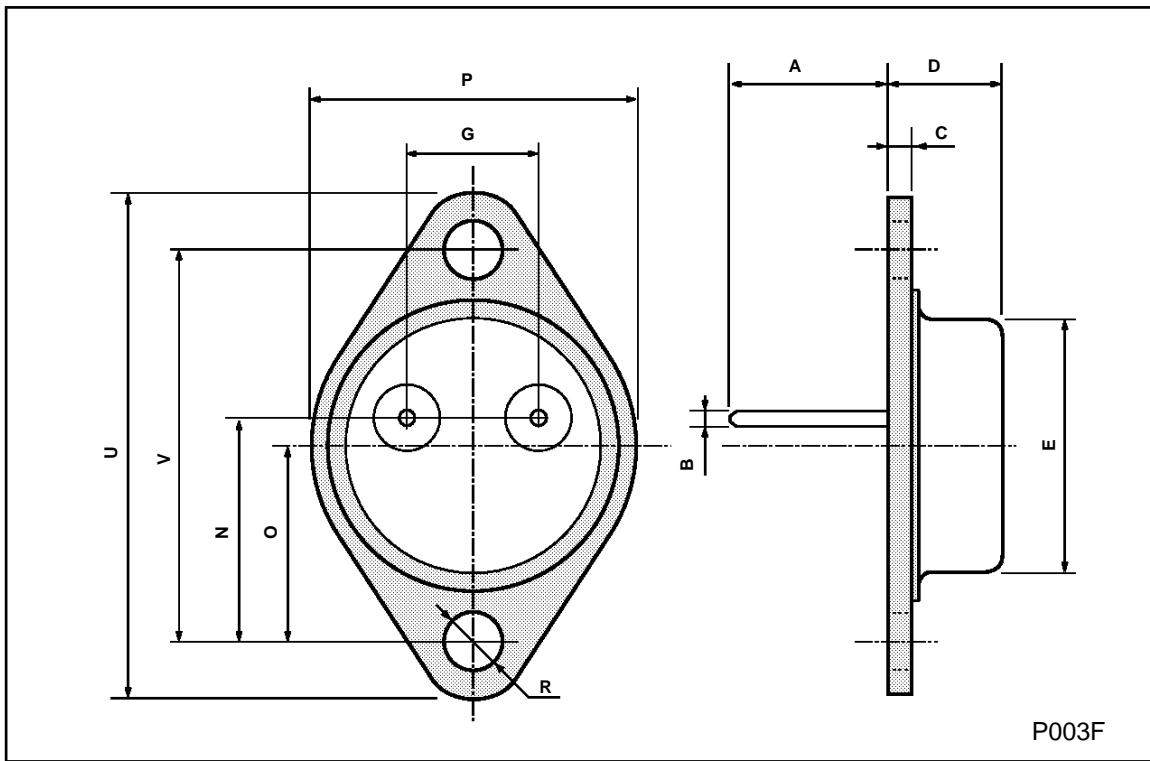


**FIGURE 4:** Sustaining Voltage Test Circuit



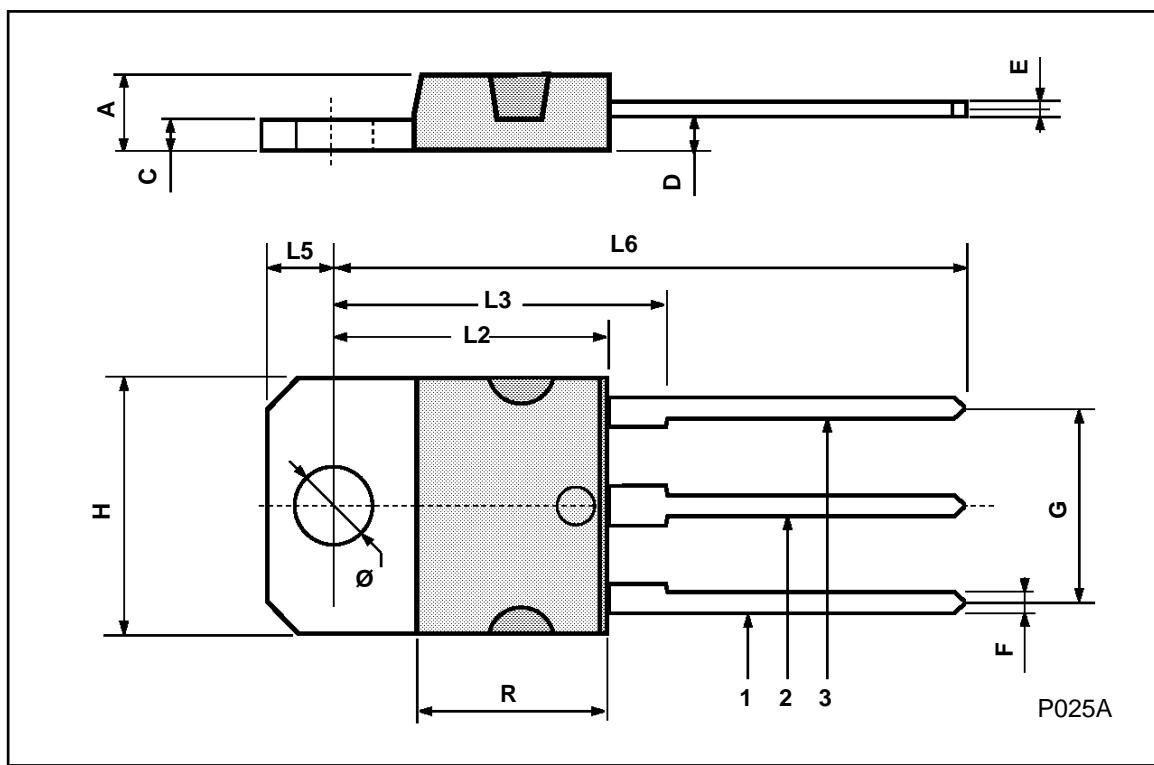
## TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



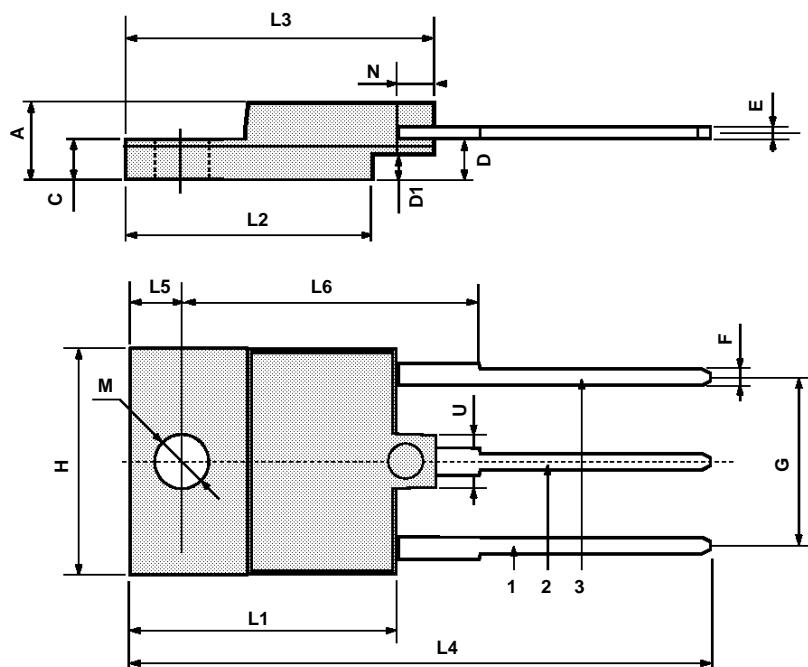
## TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		4.9	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.5			0.098	
E	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
H	14.7		15.2	0.578		0.598
L2	-		16.2	-		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	-		12.2	-		0.480
Ø	4		4.1	0.157		0.161



## ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.45		1	0.017		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	



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